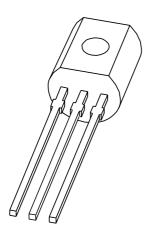
DISCRETE SEMICONDUCTORS

DATA SHEET



PH2369 NPN switching transistor

Product specification Supersedes data of 1997 May 27 1999 Apr 27





NPN switching transistor

PH2369

FEATURES

- Low current (max. 200 mA)
- Low voltage (max. 15 V).

APPLICATIONS

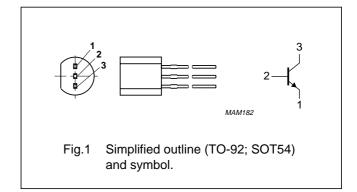
• High-speed switching.

DESCRIPTION

NPN switching transistor in a TO-92; SOT54 plastic package.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	40	V
V _{CEO}	collector-emitter voltage	open base	_	15	V
V _{EBO}	emitter-base voltage	open collector	_	4.5	V
I _C	collector current (DC)		_	200	mA
I _{CM}	peak collector current		_	300	mA
I _{BM}	peak base current		_	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	_	500	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	250	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

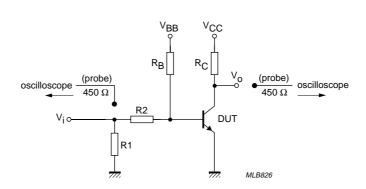
CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 20 V	_	400	nA
		I _E = 0; V _{CB} = 20 V; T _j = 125 °C	_	30	μΑ
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = 4 V	_	100	nA
h _{FE}	DC current gain	I _C = 10 mA; V _{CE} = 1 V	40	120	
		$I_C = 10 \text{ mA}; V_{CE} = 1 \text{ V}; T_{amb} = -55 ^{\circ}\text{C}$	20	_	
		I _C = 100 mA; V _{CE} = 2 V	20	_	
V _{CEsat}	collector-emitter saturation voltage	I _C = 10 mA; I _B = 1 mA	_	250	mV
V _{BEsat}	base-emitter saturation voltage	I _C = 10 mA; I _B = 1 mA	700	850	mV
C _c	collector capacitance	I _E = i _e = 0; V _{CB} = 5 V; f = 1 MHz	_	4	pF
C _e	emitter capacitance	$I_C = i_c = 0$; $V_{EB} = 1 \text{ V}$; $f = 1 \text{ MHz}$	_	4.5	pF
f _T	transition frequency	I _C = 10 mA; V _{CE} = 10 V; f = 100 MHz	500	_	MHz
Switching t	imes (between 10% and 90% levels	s)	-		
t _{on}	turn-on time	$I_{Con} = 10 \text{ mA}; I_{Bon} = 3 \text{ mA}; I_{Boff} = -1.5 \text{ mA};$	_	10	ns
t _d	delay time	see Fig.2 test conditions A	_	4	ns
t _r	rise time		_	6	ns
t _{off}	turn-off time		_	20	ns
t _s	storage time		_	10	ns
t _f	fall time		_	10	ns
t _{on}	turn-on time	$I_{Con} = 100 \text{ mA}; I_{Bon} = 40 \text{ mA}; I_{Boff} = -20 \text{ mA};$	_	13	ns
t _{off}	turn-off time	see Fig.2 test conditions B	_	35	ns

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Test conditions A.

$$\begin{split} &V_i = 0.5 \text{ to } 4.2 \text{ V; } T = 500 \text{ } \mu\text{s; } t_p = 10 \text{ } \mu\text{s; } t_f = t_f \leq 3 \text{ ns.} \\ &R1 = 56 \text{ } \Omega; \text{ } R2 = 1 \text{ } k\Omega; \text{ } R_B = 1 \text{ } k\Omega; \text{ } R_C = 270 \text{ } \Omega. \\ &V_{BB} = 0.2 \text{ V; } V_{CC} = 2.7 \text{ V.} \\ &Oscilloscope: input impedance \text{ } Z_i = 50 \text{ } \Omega. \end{split}$$

Test conditions B.

$$\begin{split} &V_i = 0.5 \text{ to } 4.52 \text{ V; } T = 200 \text{ } \mu\text{s; } t_p = 10 \text{ } \mu\text{s; } t_f = t_f \leq 3 \text{ ns.} \\ &R1 = 100 \text{ } \Omega; \text{ } R2 = 68 \text{ } \Omega; \text{ } R_B = 390 \text{ } \Omega; \text{ } R_C = 47 \text{ } \Omega. \\ &V_{BB} = -3 \text{ } V; \text{ } V_{CC} = 4.6 \text{ } V. \\ &Oscilloscope: input impedance \text{ } Z_i = 50 \text{ } \Omega. \end{split}$$

Fig.2 Test circuit for switching times.

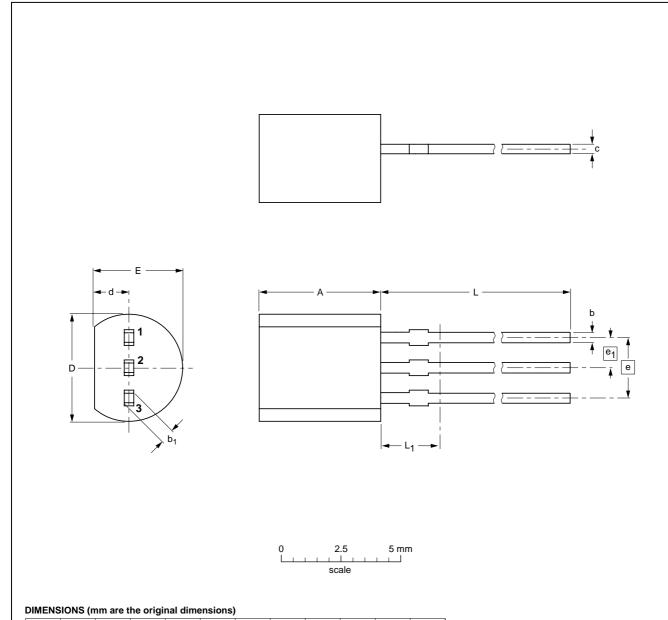
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PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	A	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾
mm	5.2 5.0	0.48 0.40	0.66 0.56	0.45 0.40	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

	OUTLINE		REFERENCES			EUROPEAN ISSUE DATE	
VERSION		IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
	SOT54		TO-92	SC-43			97-02-28

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DEFINITIONS

Data sheet status			
Objective specification	This data sheet contains target or goal specifications for product development.		
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.		
Product specification	This data sheet contains final product specifications.		
Limiting values			
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or			

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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NPN switching transistor

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